

## NPN MEDIUM POWER TRANSISTORS

### Features

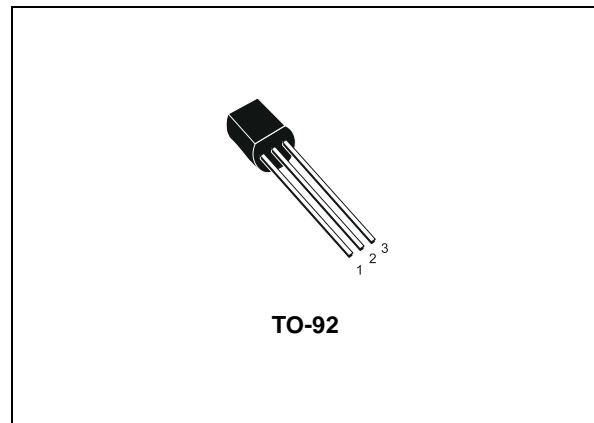
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- IN COMPLIANCE WITH THE 2002/93/EC EUROPEAN DIRECTIVE

### Applications

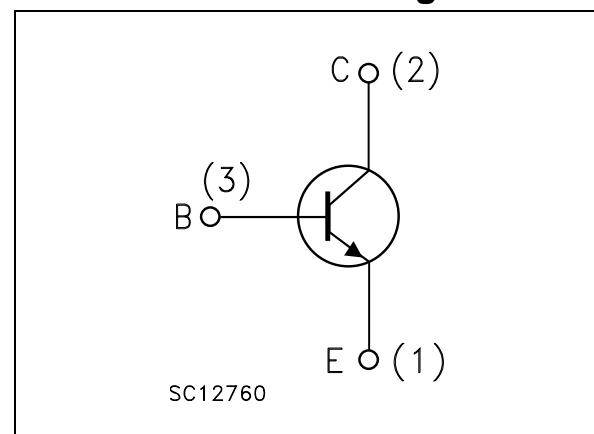
- VOLTAGE REGULATION
- RELAY DRIVER
- GENERIC SWITCH

### Description

The STX724 is a NPN transistor manufactured using planar Technology resulting in rugged high performance devices.



### Internal Schematic Diagram



### Order codes

| Part Number | Marking | Package | Packing |
|-------------|---------|---------|---------|
| STX724      | X724    | TO-92   | BULK    |

# 1 Electrical Ratings

**Table 1. Absolute Maximum Rating**

| Symbol    | Parameter                               | Value      | Unit |
|-----------|---|------------|------|
| $V_{CBO}$ | Collector-Base Voltage ( $I_E = 0$ )    | 60         | V    |
| $V_{CEO}$ | Collector-Emitter Voltage ( $I_B = 0$ ) | 30         | V    |
| $V_{EBO}$ | Collector-Base Voltage ( $I_C = 0$ )    | 5          | V    |
| $I_C$     | Collector Current                       | 3          | A    |
| $I_{CM}$  | Collector Peak Current ( $t_p < 5ms$ )  | 6          | A    |
| $I_B$     | Base Current                            | 1          | A    |
| $I_{BM}$  | Base Peak Current ( $t_p < 5ms$ )       | 2          | A    |
| $P_{TOT}$ | Total dissipation at $T_c = 25^\circ C$ | 0.9        | W    |
| $T_{STG}$ | Storage Temperature                     | -65 to 150 | °C   |
| $T_J$     | Max. Operating Junction Temperature     |            |      |

**Table 2. Thermal Data**

| Symbol         | Parameter                            | Value | Unit |
|----------------|--------------------------------------|-------|------|
| $R_{thj-case}$ | Thermal Resistance Junction-Case Max | 44.6  | °C/W |
| $R_{thj-amb}$  | Thermal Resistance Junction-Amb Max  | 139   | °C/W |

## 2 Electrical Characteristics

**Table 3. Electrical Characteristics** ( $T_{CASE} = 25^{\circ}C$ ; unless otherwise specified)

| Symbol                         | Parameter  | Test Conditions   | Min.            | Typ. | Max.              | Unit        |
|--------------------------------|--|---|-----------------|------|-------------------|-------------|
| $I_{CES}$                      | Collector Cut-off Current<br>( $V_{BE} = 0$ )        | $V_{CE} = 60V$  |                 |      | 10                | $\mu A$     |
| $I_{CEO}$                      | Collector Cut-off Current<br>( $I_B = 0$ )           | $V_{CE} = 30V$  |                 |      | 100               | $\mu A$     |
| $I_{EBO}$                      | Emitter Cut-off Current<br>( $I_C = 0$ )             | $V_{EB} = 5V$   |                 |      | 10                | $\mu A$     |
| $V_{(BR)CBO}$                  | Collector-Base<br>Breakdown Voltage ( $I_E = 0$ )    | $I_C = 100\mu A$  | 60              |      |                   | V           |
| $V_{(BR)CEO}$<br><i>Note 1</i> | Collector-Emitter Breakdown<br>Voltage ( $I_B = 0$ ) | $I_C = 10\text{ mA}$  | 30              |      |                   | V           |
| $V_{(BR)EBO}$                  | Collector-Emitter Breakdown<br>Voltage ( $I_C = 0$ ) | $I_E = 100\mu A$  | 5               |      |                   | V           |
| $V_{CE(sat)}$<br><i>Note 1</i> | Collector-Emitter Saturation<br>Voltage              | $I_C = 1\text{ A}$ $I_B = 50\text{ mA}$<br>$I_C = 2\text{ A}$ $I_B = 100\text{ mA}$<br>$I_C = 3\text{ A}$ $I_B = 150\text{ mA}$     |                 |      | 0.4<br>0.7<br>1.1 | V<br>V<br>V |
| $V_{BE(sat)}$<br><i>Note 1</i> | Base-Emitter Saturation Voltage                      | $I_C = 2\text{ A}$ $I_B = 100\text{ mA}$  |                 |      | 1.2               | V           |
| $h_{FE}$                       | DC Current Gain                                      | $I_C = 100\text{ mA}$ $V_{CE} = 2\text{ V}$<br>$I_C = 1\text{ A}$ $V_{CE} = 2\text{ V}$<br>$I_C = 3\text{ A}$ $V_{CE} = 2\text{ V}$ | 100<br>80<br>30 |      | 300               |             |
| $f_T$                          | Transistor Frequency                                 | $V_{CE} = 10\text{ V}$ $I_C = 0.1\text{ A}$   |                 | 100  |                   | MHz         |

1 Pulsed duration = 300  $\mu s$ , duty cycle  $\leq 1.5\%$ .

## 2.1 Electrical characteristics (curve)

Figure 1. DC Current Gain

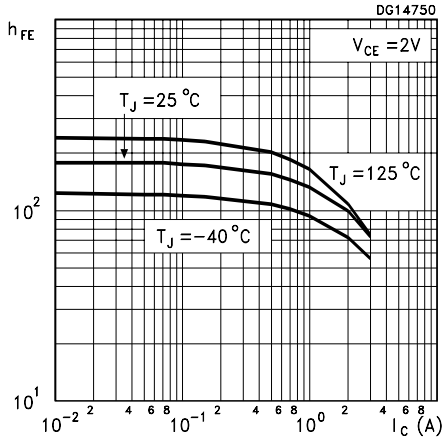


Figure 2. DC Current Gain

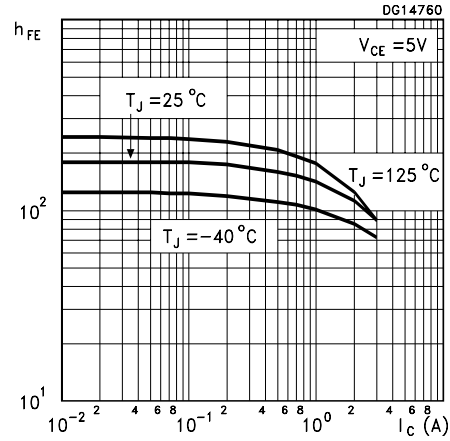


Figure 3. Collector-emitter saturation voltage Figure 4. Base-emitter saturation voltage

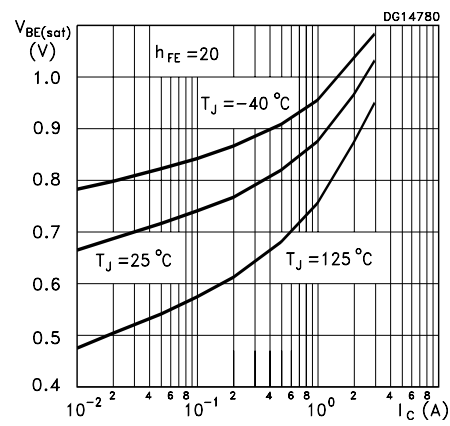
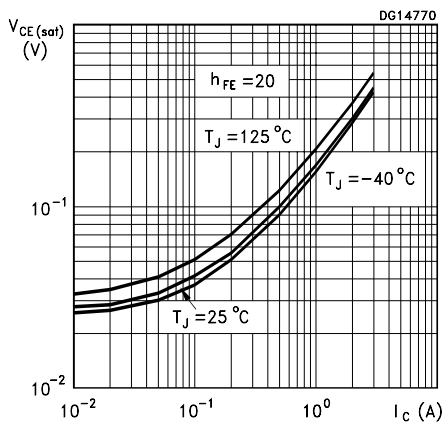


Figure 5. Switching times on resistive load

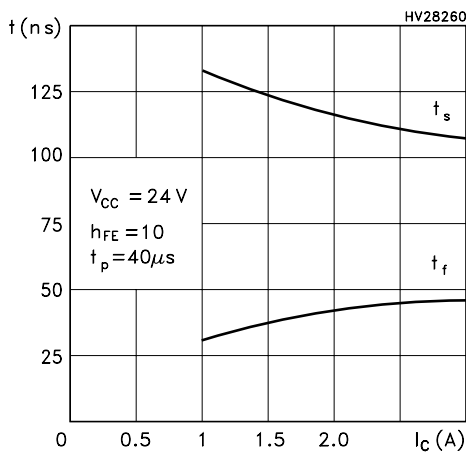


Figure 6. Switching times resistive on load

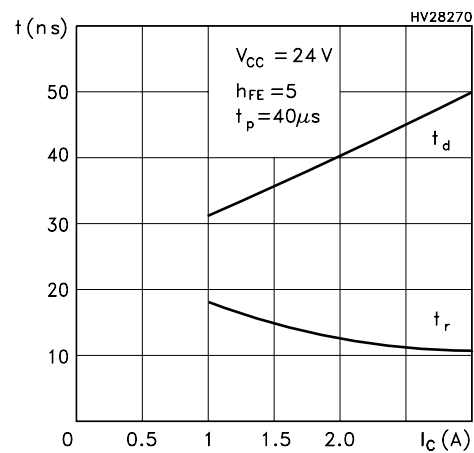
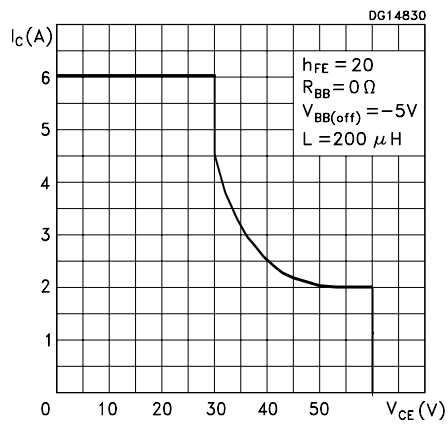


Figure 7. Reverse biased area

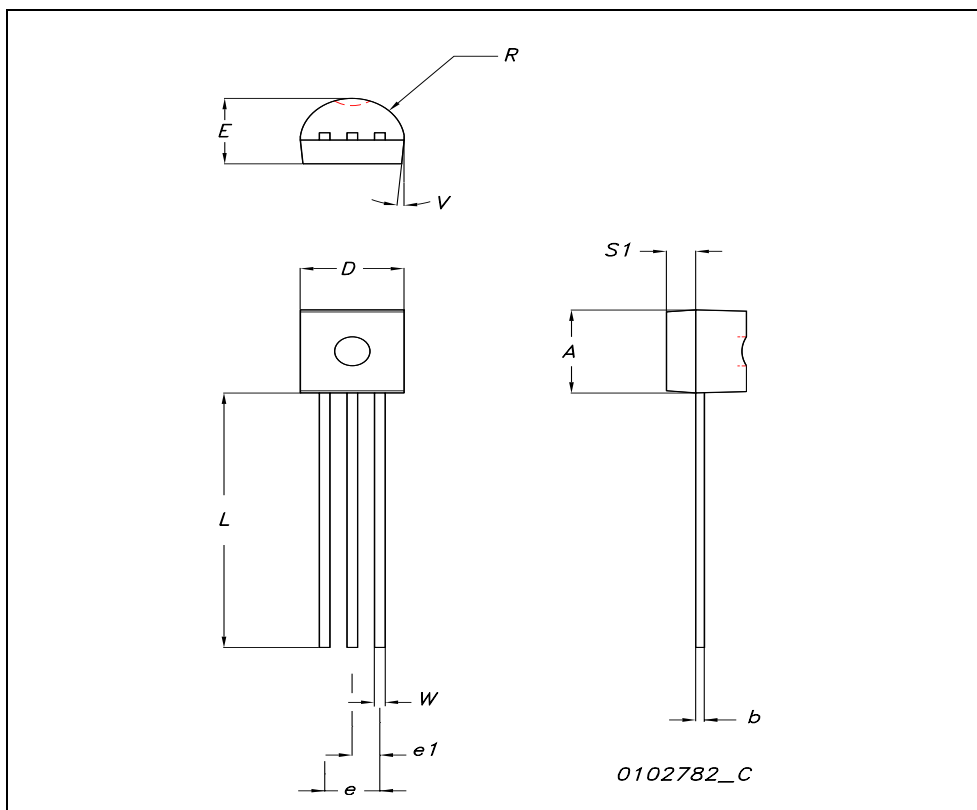


### 3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**TO-92 MECHANICAL DATA**

| DIM. | mm.   |      |       | inch  |      |       |
|------|-------|------|-------|-------|------|-------|
|      | MIN.  | TYP. | MAX.  | MIN.  | TYP. | MAX.  |
| A    | 4.32  |      | 4.95  | 0.170 |      | 0.194 |
| b    | 0.36  |      | 0.51  | 0.014 |      | 0.020 |
| D    | 4.45  |      | 4.95  | 0.175 |      | 0.194 |
| E    | 3.30  |      | 3.94  | 0.130 |      | 0.155 |
| e    | 2.41  |      | 2.67  | 0.094 |      | 0.105 |
| e1   | 1.14  |      | 1.40  | 0.044 |      | 0.055 |
| L    | 12.70 |      | 15.49 | 0.50  |      | 0.610 |
| R    | 2.16  |      | 2.41  | 0.085 |      | 0.094 |
| S1   | 0.92  |      | 1.52  | 0.036 |      | 0.060 |
| W    | 0.41  |      | 0.56  | 0.016 |      | 0.022 |
| V    |       | 5°   |       |       | 5°   |       |



## 4 Revision History

| Date        | Revision | Changes       |
|-------------|----------|---------------|
| 17-Oct-2005 | 1        | First release |



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